

AMENDMENTS TO THE CLAIMS

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-6. (cancelled)

7. (original): A method of making a semiconductor device comprising:
 depositing a layer of oxide proximate a first surface of a semiconductor substrate;
 forming a gate oxide layer on the first surface, adjacent to the deposited oxide layer;
 forming a pair of active areas in the first surface, adjacent the deposited oxide layer and gate oxide layer;
 forming a gate electrode by depositing a conductive layer over the gate oxide layer;
 depositing a dielectric layer over the gate electrode, active areas, and deposited oxide layer; and
 forming electrical contacts to the pair of active areas and the gate electrode.

8. (original): The method of Claim 7, further comprising thermally growing a thermal oxide layer before depositing the layer of oxide on the first surface of the semiconductor substrate.

1 9. (original): The method of Claim 7, wherein the semiconductor substrate is
2 P type silicon.

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4 10. (original): The method of Claim 7, wherein the active areas are formed by
5 impurity implant and diffusion.

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7 11. (original): The method of Claim 7, wherein the active areas are n doped
8 regions.

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10 12. (original): The method of Claim 7, wherein the conductive layer over the
11 gate oxide layer is polysilicon.

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13 13. (original): The method of Claim 7, wherein the dielectric layer is silicon
14 dioxide.

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16 Claims 14-18 (cancelled)

17
18 19. (currently amended): A method comprising of manufacturing a fluid
19 ejection device, ~~the method comprising by:~~

20 depositing a current prevention layer proximate a first surface of a
21 semiconductor substrate; and

22 forming first and second field effect transistors (FETs), wherein each said
23 FET includes a gate electrode with associated active areas formed in the first
24 surface of the semiconductor substrate having the deposited current prevention
25 layer, wherein the current prevention layer includes a region that minimizes

1 current flow between the active areas of the first FET with respect to the active
2 areas of the second FET; and
3 forming a firing chamber above the current prevention layer.
4

5 20. (original): The method of Claim 19, wherein the current prevention layer is
6 a dielectric.
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8 21. (original): The method of Claim 19, wherein the current prevention layer is
9 an oxide.
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11 22. (currently amended): A method comprising:
12 depositing a layer of oxide proximate a first surface of a semiconductor
13 substrate;
14 exposing a portion of the first surface of the semiconductor substrate; and
15 forming a field effect transistor (FET) on the exposed portion of the first
16 surface of the substrate having the deposited oxide layer, wherein the FET
17 includes a gate electrode with associated active areas formed after the exposing in
18 the first surface of the semiconductor substrate.
19

20 23. (previously presented): A product formed by the method of Claim 22.
21

22 24. (previously presented): A method of making a semiconductor device
23 comprising:
24 depositing a layer of oxide proximate a first surface of a semiconductor
25 substrate;

1 exposing a portion of the first surface of the semiconductor substrate;
2 forming a gate oxide layer on the exposed portion of the first surface,
3 adjacent to the deposited oxide layer;
4 forming a pair of active areas in the exposed portion of the first surface,
5 adjacent the deposited oxide layer and gate oxide layer;
6 forming a gate electrode by depositing a conductive layer over the gate
7 oxide layer;
8 depositing a dielectric layer over the gate electrode, active areas, and
9 deposited oxide layer; and
10 forming electrical contacts to the pair of active areas and the gate electrode.

11
12 25. (previously presented): The method of Claim 24, further comprising
13 thermally growing a thermal oxide layer before depositing the layer of oxide on
14 the first surface of the semiconductor substrate.

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16 26. (previously presented): The method of Claim 24, wherein the
17 semiconductor substrate is P type silicon.

18
19 27. (previously presented): The method of Claim 24, wherein the active areas
20 are formed by impurity implant and diffusion.

21
22 28. (previously presented): The method of Claim 24, wherein the active areas
23 are n doped regions.
24
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1 29. (previously presented): The method of Claim 24, wherein the conductive
2 layer over the gate oxide layer is polysilicon.

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4 30. (previously presented): The method of Claim 24, wherein the dielectric
5 layer is silicon dioxide.

6
7 31. (previously presented): A semiconductor device produced by the method of
8 claim 24.

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10 32. (previously presented): A semiconductor device produced by the method
11 of claim 7.

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13 33. (previously presented): A fluid ejection device produced by the method of
14 claim 19.